INITIAL DEVELOPMENT OF A HIGH-PRESSURE CRYSTAL GROWTH FACILITY -- CENTER DIRECTOR'S DISCRETIONARY FUND FINAL REPORT (PROJECT NO. 87-25)

By F. R. Szofran, S. L. Lehoczky, S. D. Cobb, and D. C. Gillies

Space Science Laboratory
Science and Engineering Directorate

November 1993


N94-21807

Unclass

G3/76 0198121
**REPORT DOCUMENTATION PAGE**

Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503.

1. AGENCY USE ONLY (Leave blank) 2. REPORT DATE 3. REPORT TYPE AND DATES COVERED
   - November 1993
   - Technical Memorandum

4. TITLE AND SUBTITLE
   Initial Development of a High-Pressure Crystal Growth Facility -- Center Director's Discretionary Fund Final Report (Project No. 87-25)

5. FUNDING NUMBERS

6. AUTHOR(S)
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7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES)
   - George C. Marshall Space Flight Center
     - Marshall Space Flight Center, AL 35812

8. PERFORMING ORGANIZATION REPORT NUMBER

9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES)
   - National Aeronautics and Space Administration
     - Washington, D.C. 20546

10. SPONSORING/MONITORING AGENCY REPORT NUMBER
   - NASA TM-108430

11. SUPPLEMENTARY NOTES

12a. DISTRIBUTION/AVAILABILITY STATEMENT
   - Unclassified--Unlimited

12b. DISTRIBUTION CODE

13. ABSTRACT (Maximum 200 words)

   A low-cost, flexible, high-pressure (600 psi) system for crystal growth and related thermophysical properties measurements was designed, assembled, and tested. The furnace system includes a novel, magnetically coupled translation mechanism that eliminates the need for a high-pressure mechanical feedthru. The system is currently being used for continuing crystal growth experiments and thermophysical properties measurements on several material systems including \( \text{Hg}_1-x\text{Cd}_x\text{Te} \), \( \text{Hg}_1-x\text{Zn}_x\text{Te} \), and \( \text{Hg}_1-x\text{Zn}_x\text{Se} \).

14. SUBJECT TERMS
   - High-Pressure Crystal Growth Furnace,
     Thermophysical Properties Measurements

15. NUMBER OF PAGES
   - 9

16. PRICE CODE
   - NTIS

17. SECURITY CLASSIFICATION OF REPORT
   - Unclassified

18. SECURITY CLASSIFICATION OF THIS PAGE
   - Unclassified

19. SECURITY CLASSIFICATION OF ABSTRACT
   - Unclassified

20. LIMITATION OF ABSTRACT
   - Unlimited

NSN 7540-01-280-5500

Standard Form 298 (Rev. 2-89)
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OBJECTIVES AND BACKGROUND OF THE PROJECT

This project initiated the development of a high-pressure facility for future flight experiments and commercial scale crystal growth to facilitate the measurement of thermophysical properties and growth of larger diameter crystals of semiconducting compounds having a very high vapor pressure at the growth temperature. Many of the compound semiconductors currently being developed to meet unique photonic and electronic materials requirements have vapor pressures of tens of atmospheres at the growth temperatures. These materials include all of the important narrow band-gap solid solution semiconducting alloy systems such as Hg_{1-x}Cd_xTe, Hg_{1-x}Mn_xTe, Hg_{1-x}Zn_xTe, and related compounds which are the subjects of several approved space flight experiments. Most III-V compounds such as GaAs, also the subject of a flight experiment, and InP and their alloys also have high vapor pressures. The crystal growth of any of these materials in commercially viable sizes can be done more efficiently, if at all, in a high-pressure furnace. For example, Hg_{1-x}Cd_xTe alloys are typically grown in fused silica ampoules in diameters up to about 1.5 cm, but the vapor pressure prohibits growth of larger-diameter material in ambient pressure apparatus. Requirements are projected for diameters 4 to 5 times larger than the capabilities provided by presently available apparatus, and the long lead times for developing such apparatus require that development begin as soon as possible. Such a facility is being considered for inclusion in the Space Station Furnace Facility being developed for use on Space Station Freedom.

APPROACH AND DESCRIPTION OF THE APPARATUS

A high-pressure furnace in which the furnace shell is also the pressure vessel has been described by Ciszek and Evans [1]. A modified version of that furnace, shown in Figure 1, has been constructed. All necessary instrumentation is included for pressure control, temperature control, translation, and temperature measurement to carry out experiments in the furnace including crystal growth by directional solidification (Bridgman) or the quench-anneal method and differential thermal analysis for phase diagram determination of II-VI Hg compounds such as Hg_{1-x}Zn_xTe and Hg_{1-x}Zn_xSe which are materials being investigated in a current flight project.

The furnace has high- and low-temperature zones, a gradient zone, and a booster heater at the high-temperature end of the gradient zone to enable the achievement of higher temperature gradients. The actual bore diameter is 22 mm which will permit sample containers to be used with outside diameters up to 20 mm. This, in turn, will allow the growth of ingots up to 18 mm in diameter. An example temperature profile used to grow Hg_{0.8}Cd_{0.2}Te is shown in Figure 2. An additional feature of the design is that the furnace core and insulation package are modular so that replacing the core to achieve additional thermal profiles is straightforward and nondestructive. Thus, additional cores could be constructed and easily interchanged as required for different experiments.
The furnace system includes a novel translation mechanism that uses magnetic coupling and which eliminates the need for a high-pressure mechanical feedthru. The translation rate range is determined by a combination of a dc motor and gear reduction box connected to a ball lead screw. Thus, any translation rate of interest for crystal growth can be achieved.

The argon gas handling system was safety tested up to 1100 psi but pressures above 600 psi will not be needed in the laboratory. The pressure inside the furnace is under closed-loop control and can be programmed to follow a pressure profile such as the pressure inside an ampoule during the temperature profile imposed during crystal growth or thermophysical properties measurements. A schematic diagram of the furnace control functions is shown in Figure 3. The pressure system has been used successfully during several Hg$_{0.8}$Cd$_{0.2}$Te crystal growth experiments.

**RESULTS**

For a modest overall cost, a highly functional and safe high-pressure furnace system has been designed, assembled, and tested. In addition to the individual tests of the thermal and pressure subsystems, two Hg$_{0.8}$Cd$_{0.2}$Te ingots have been directionally solidified in the furnace as a system test. The temperature profile is shown in Figure 2 and the pressure profile was designed to equalize the pressure on either side of the ampoule wall. The pressure inside the ampoule was calculated from the known pressure over Hg$_{0.8}$Cd$_{0.2}$Te [2] and is approximately one-third the equilibrium vapor pressure of pure mercury. Other parameters are given in the following table.
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Figure 2. Furnace thermal profile suitable for growing $\text{Hg}_{0.2}\text{Cd}_{0.8}\text{Te}$. 
Figure 3. Overall schematic diagram of the high-pressure furnace system.
SUMMARY

The project has shown that a low-cost, flexible, high-pressure system for crystal growth and related thermophysical properties measurements can be assembled. The system is currently being used for continuing crystal growth experiments and thermophysical properties measurements on several material systems including Hg$_{1-x}$Cd$_x$Te, Hg$_{1-x}$Zn$_x$Te, and Hg$_{1-x}$Zn$_x$Se. A pending proposal would use the system for Hg$_{1-x}$Mn$_x$Te.

REFERENCES


APPROVAL

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This report has been reviewed for technical accuracy and contains no information concerning national security or nuclear energy activities or programs. The report, in its entirety, is unclassified.

[Signature]
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Director, Space Science Laboratory

U.S. GOVERNMENT PRINTING OFFICE 1993 533–108 / 80146